





#### 100V NPN MEDIUM POWER TRANSISTOR IN SOT223

#### **Features**

- BV<sub>CEO</sub> > 100V
- I<sub>C</sub> = 6A high Continuous Collector Current
- I<sub>CM</sub> = 10A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < 150mV @ 2A</li>
- $R_{CE(sat)} = 50 m\Omega$  for a Low Equivalent On-Resistance
- h<sub>FE</sub> Specified Up to 10A for a High Gain Hold Up
- Complementary PNP Type: FZT953
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

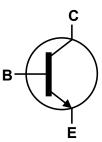
#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 63
- Weight: 0.112 grams (approximate)

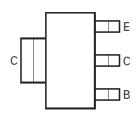




Top View



Device Symbol



Top View Pin-Out

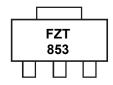
# Ordering Information (Note 4)

Ī	Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	FZT853TA	AEC-Q101	FZT853	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com

## **Marking Information**



FZT853 = Product Type Marking Code





**FZT853** 

#### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	200	V
Collector-Emitter Voltage	$V_{CEO}$	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	lc	6	Α
Peak Pulse Current	I <sub>CM</sub>	10	А

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)		3.0 24	W	
Linear derating factor	(Note 6)	- P <sub>D</sub>	1.6 12.8	mW/°C	
Thermal Desistance Junction to Ambient	(Note 5)	$R_{ heta JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	78	°C/W	
Thermal Resistance Junction to Lead (Note 7)		$R_{ heta JL}$	8.84		
Operating and Storage Temperature Range	•	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

### ESD Ratings (Note 8)

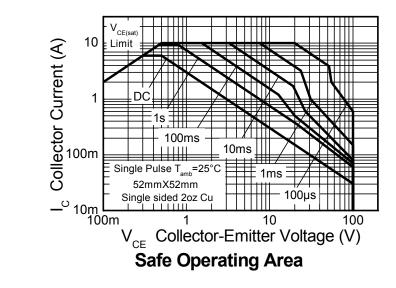
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

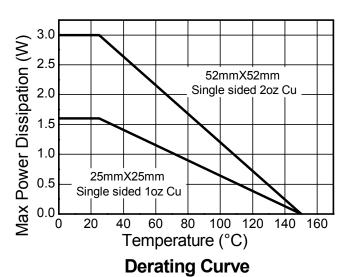
Notes:

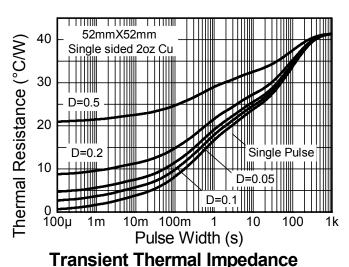
- 5. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; device measured when operating in steady state condition.
- 6. Same as note (5), except the device is mounted on 50mm X 50mm single sided 2oz weight copper.
  7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

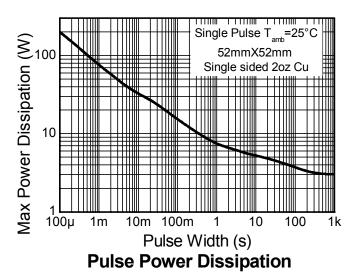


# **Thermal Characteristics and Derating Information**













**FZT853** 

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

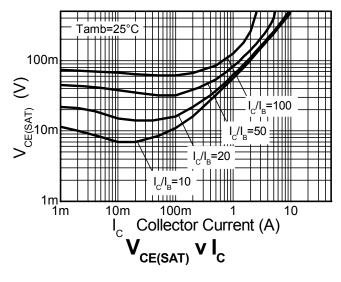
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_CBO$	200	300	-	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	200	300	_	V	$I_C = 1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	100	120	_	V	I <sub>C</sub> = 1mA
Emitter-Base Breakdown Voltage	$BV_EBO$	7	8.1	_	V	I <sub>E</sub> = 100μA
Collector Cut-off Current	Ісво	-	<1	10	nA	V <sub>CB</sub> = 150V
Collector Cut-on Current		-	_	1	μΑ	V <sub>CB</sub> = 150V, T <sub>A</sub> = +100°C
Collector Cut-off Current	lone	-	<1	10	nA	$V_{CB}$ = 150V, $R_B \le 1k\Omega$
Collector Cut-on Current	I <sub>CER</sub>	-	_	1	μΑ	V <sub>CB</sub> = 150V, T <sub>A</sub> = +100°C
Emitter Cut-off Current	I <sub>EBO</sub>	-	<1	10	nA	V <sub>EB</sub> = 6V
	h <sub>FE</sub>	100	200	-		$I_C$ = 10mA, $V_{CE}$ = 2V
DC Current Coin (Note 0)		100	200	300	Ι	$I_C = 2A$ , $V_{CE} = 2V$
DC Current Gain (Note 9)		50	100	_		I <sub>C</sub> = 4A, V <sub>CE</sub> = 2V
		20	30	-		I <sub>C</sub> = 10A, V <sub>CE</sub> = 2V
	V <sub>CE(sat)</sub>	-	14	50		I <sub>C</sub> = 100mA, I <sub>B</sub> = 5mA
Collector-Emitter Saturation Voltage (Note 9)		-	100	150	mV	I <sub>C</sub> = 2A, I <sub>B</sub> = 100mA
		-	250	340		I <sub>C</sub> = 5A, I <sub>B</sub> = 500mA
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	-	1050	1250	mV	I <sub>C</sub> = 5A, I <sub>B</sub> = 500mA
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	-	900	1100	mV	I <sub>C</sub> = 5A, V <sub>CE</sub> = 2V
Current Gain-Bandwidth Product (Note 9)	f⊤	-	130	-	MHz	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 10V, f = 50MHz
Output Capacitance (Note 9)	C <sub>obo</sub>	_	35	_	pF	V <sub>CB</sub> = 10V, f = 1MHz
Switching Times	t <sub>on</sub>	-	50	_	no	$I_C = 1A$ , $V_{CC} = 10V$ ,
Switching Times	t <sub>off</sub>	=	1650	=	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$

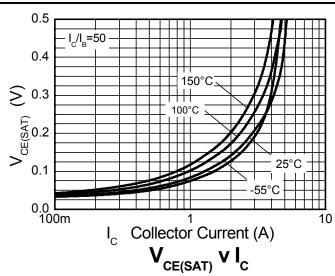
Notes: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%

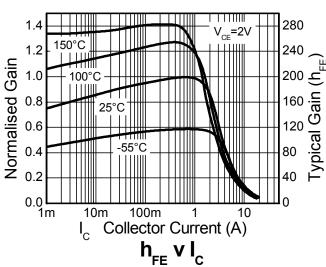


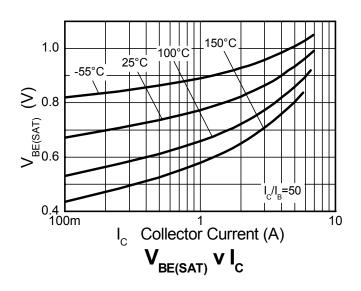
**FZT853** 

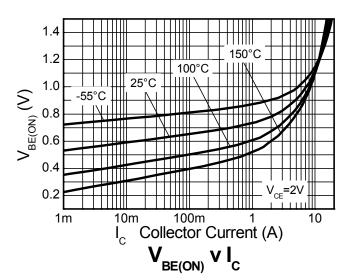
### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)







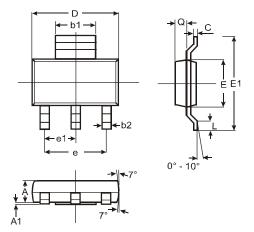






# **Package Outline Dimensions**

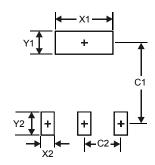
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b1	2.90	3.10	3.00			
b2	0.60	0.80	0.70			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е			4.60			
e1	_	_	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
X1	3.3		
X2	1.2		
Y1	1.6		
Y2	1.6		
C1	6.4		
C2	2.3		





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